

Sidong Lei

List of Publications by Year in descending order

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329
papers

26,279
citations

8732

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all docs

335
docs citations

335
times ranked

25167
citing authors

#	ARTICLE	IF	CITATIONS
1	Vertical and in-plane heterostructures from WS ₂ /MoS ₂ monolayers. Nature Materials, 2014, 13, 1135-1142.	13.3	1,918
2	Vapour phase growth and grain boundary structure of molybdenum disulphide atomic layers. Nature Materials, 2013, 12, 754-759.	13.3	1,590
3	Blowing magnetic skyrmion bubbles. Science, 2015, 349, 283-286.	6.0	1,177
4	Direct observation of the skyrmion Hall effect. Nature Physics, 2017, 13, 162-169.	6.5	858
5	In-plane heterostructures of graphene and hexagonal boron nitride with controlled domain sizes. Nature Nanotechnology, 2013, 8, 119-124.	15.6	796
6	Magnetization switching through giant spin-orbit torque in a magnetically doped topological insulator heterostructure. Nature Materials, 2014, 13, 699-704.	13.3	773
7	Switching of perpendicular magnetization by spin-orbit torques in the absence of external magnetic fields. Nature Nanotechnology, 2014, 9, 548-554.	15.6	753
8	Resistive switching materials for information processing. Nature Reviews Materials, 2020, 5, 173-195.	23.3	668
9	Evolution of the Electronic Band Structure and Efficient Photo-Detection in Atomic Layers of InSe. ACS Nano, 2014, 8, 1263-1272.	7.3	534
10	Two-Step Growth of Two-Dimensional WSe ₂ /MoSe ₂ Heterostructures. Nano Letters, 2015, 15, 6135-6141.	4.5	479
11	Direct Laser-Patterned Micro-Supercapacitors from Paintable MoS ₂ Films. Small, 2013, 9, 2905-2910.	5.2	455
12	Scale-Invariant Quantum Anomalous Hall Effect in Magnetic Topological Insulators beyond the Two-Dimensional Limit. Physical Review Letters, 2014, 113, 137201.	2.9	453
13	Chemical Vapor Deposition of Thin Crystals of Layered Semiconductor SnS ₂ for Fast Photodetection Application. Nano Letters, 2015, 15, 506-513.	4.5	430
14	Synthesis and Photoresponse of Large GaSe Atomic Layers. Nano Letters, 2013, 13, 2777-2781.	4.5	381
15	Two-dimensional spintronics for low-power electronics. Nature Electronics, 2019, 2, 274-283.	13.1	334
16	Wafer-scale monodomain films of spontaneously aligned single-walled carbon nanotubes. Nature Nanotechnology, 2016, 11, 633-638.	15.6	292
17	Room-Temperature Creation and Spin-Orbit Torque Manipulation of Skyrmions in Thin Films with Engineered Asymmetry. Nano Letters, 2016, 16, 1981-1988.	4.5	275
18	Precise Quantization of the Anomalous Hall Effect near Zero Magnetic Field. Physical Review Letters, 2015, 114, 187201.	2.9	255

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19	An Atomically Layered InSe Avalanche Photodetector. Nano Letters, 2015, 15, 3048-3055.	4.5	253
20	Strong Rashba-Edelstein Effect-Induced Spin-Orbit Torques in Monolayer Transition Metal Dichalcogenide/Ferromagnet Bilayers. Nano Letters, 2016, 16, 7514-7520.	4.5	247
21	Giant electric-field-induced reversible and permanent magnetization reorientation on magnetoelectric Ni/(011) [Pb(Mg _{1/3} Nb _{2/3})O ₃](1-x)[PbTiO ₃] _x heterostructure. Applied Physics Letters, 2011, 98, 012504.	1.5	236
22	Piezoelectric effect in chemical vapour deposition-grown atomic-monolayer triangular molybdenum disulfide piezotronics. Nature Communications, 2015, 6, 7430.	5.8	233
23	Room-Temperature Skyrmion Shift Device for Memory Application. Nano Letters, 2017, 17, 261-268.	4.5	227
24	Electric-field control of spin-orbit torque in a magnetically doped topological insulator. Nature Nanotechnology, 2016, 11, 352-359.	15.6	212
25	Effect of phonon confinement on the thermoelectric figure of merit of quantum wells. Journal of Applied Physics, 1998, 84, 6149-6153.	1.1	209
26	Spin Wave Magnetic NanoFabric: A New Approach to Spin-Based Logic Circuitry. IEEE Transactions on Magnetism, 2008, 44, 2141-2152.	1.2	199
27	Surface functionalization of two-dimensional metal chalcogenides by Lewis acid-base chemistry. Nature Nanotechnology, 2016, 11, 465-471.	15.6	197
28	Proximity Induced High-Temperature Magnetic Order in Topological Insulator - Ferrimagnetic Insulator Heterostructure. Nano Letters, 2014, 14, 3459-3465.	4.5	192
29	Photoluminescence Quenching and Charge Transfer in Artificial Heterostacks of Monolayer Transition Metal Dichalcogenides and Few-Layer Black Phosphorus. ACS Nano, 2015, 9, 555-563.	7.3	183
30	Optoelectronic Memory Using Two-Dimensional Materials. Nano Letters, 2015, 15, 259-265.	4.5	163
31	Electrical spin injection and transport in germanium. Physical Review B, 2011, 84, .	1.1	158
32	Metallic 1T phase source/drain electrodes for field effect transistors from chemical vapor deposited MoS ₂ . APL Materials, 2014, 2, .	2.2	155
33	Electrical control of reversible and permanent magnetization reorientation for magnetoelectric memory devices. Applied Physics Letters, 2011, 98, .	1.5	153
34	Synthesis of Millimeter-Scale Transition Metal Dichalcogenides Single Crystals. Advanced Functional Materials, 2016, 26, 2009-2015.	7.8	152
35	Electrical Detection of Spin-Polarized Surface States Conduction in (Bi _{0.53} Sb _{0.47}) ₂ Te ₃ Topological Insulator. Nano Letters, 2014, 14, 5423-5429.	4.5	150
36	Alleviation of Fermi-level pinning effect on metal/germanium interface by insertion of an ultrathin aluminum oxide. Applied Physics Letters, 2008, 93, .	1.5	147

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37	Review of 3D topological insulator thin-film growth by molecular beam epitaxy and potential applications. <i>Physica Status Solidi - Rapid Research Letters</i> , 2013, 7, 50-63.	1.2	145
38	Electric-field-induced spin wave generation using multiferroic magnetoelectric cells. <i>Applied Physics Letters</i> , 2014, 104, 082403.	1.5	144
39	Robust bi-stable memory operation in single-layer graphene ferroelectric memory. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	140
40	Charge-carrier dynamics in hybrid plasmonic organic solar cells with Ag nanoparticles. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	138
41	Tailoring exchange couplings in magnetic topological-insulator/antiferromagnet heterostructures. <i>Nature Materials</i> , 2017, 16, 94-100.	13.3	137
42	Metal-to-insulator switching in quantum anomalous Hall states. <i>Nature Communications</i> , 2015, 6, 8474.	5.8	136
43	Non-volatile magnonic logic circuits engineering. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	135
44	Tailoring the Physical Properties of Molybdenum Disulfide Monolayers by Control of Interfacial Chemistry. <i>Nano Letters</i> , 2014, 14, 1354-1361.	4.5	129
45	Room-Temperature Spin-Orbit Torque from Topological Surface States. <i>Physical Review Letters</i> , 2019, 123, 207205.	2.9	129
46	Competing Weak Localization and Weak Antilocalization in Ultrathin Topological Insulators. <i>Nano Letters</i> , 2013, 13, 48-53.	4.5	128
47	Epitaxial growth of Bi ₂ Se ₃ topological insulator thin films on Si (111). <i>Journal of Applied Physics</i> , 2011, 109, 109101.	1.1	126
48	Stability, electronic, and magnetic properties of the magnetically doped topological insulators Bi ₂ Te ₃ and Bi ₂ Se ₃ . <i>Physical Review B</i> , 2011, 84, 040401.	1.1	126
49	Synthesis of large-scale atomic-layer SnS ₂ through chemical vapor deposition. <i>Nano Research</i> , 2017, 10, 2386-2394.	5.8	124
50	Imaging the motion of electrons across semiconductor heterojunctions. <i>Nature Nanotechnology</i> , 2017, 12, 36-40.	15.6	124
51	Above Room-Temperature Ferromagnetism in Wafer-Scale Two-Dimensional van der Waals Fe ₃ GeTe ₂ Tailored by a Topological Insulator. <i>ACS Nano</i> , 2020, 14, 10045-10053.	7.3	124
52	Giant spin-torque diode sensitivity in the absence of bias magnetic field. <i>Nature Communications</i> , 2016, 7, 11259.	5.8	123
53	VOLTAGE-CONTROLLED MAGNETIC ANISOTROPY IN SPINTRONIC DEVICES. <i>Spin</i> , 2012, 02, 1240002.	0.6	122
54	Strain-Induced Electronic Structure Changes in Stacked van der Waals Heterostructures. <i>Nano Letters</i> , 2016, 16, 3314-3320.	4.5	122

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55	Magnetization switching through spin-Hall-effect-induced chiral domain wall propagation. <i>Physical Review B</i> , 2014, 89, .	1.1	121
56	Origin of interfacial perpendicular magnetic anisotropy in MgO/CoFe/metallic capping layer structures. <i>Scientific Reports</i> , 2015, 5, 18173.	1.6	120
57	Temperature dependence of the voltage-controlled perpendicular anisotropy in nanoscale MgO CoFeB Ta magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	119
58	Topological Hall effect at above room temperature in heterostructures composed of a magnetic insulator and a heavy metal. <i>Nature Electronics</i> , 2019, 2, 182-186.	13.1	117
59	Interfacial Dzyaloshinskii-Moriya Interaction: Effect of $\frac{d}{d}$ Band Filling and Correlation with Spin Mixing Conductance. <i>Physical Review Letters</i> , 2018, 120, 157204.	2.9	116
60	Interplay between Different Magnetisms in Cr-Doped Topological Insulators. <i>ACS Nano</i> , 2013, 7, 9205-9212.	7.3	114
61	Towards van der Waals Epitaxial Growth of GaAs on Si using a Graphene Buffer Layer. <i>Advanced Functional Materials</i> , 2014, 24, 6629-6638.	7.8	113
62	Vertical Graphene-Base Hot-Electron Transistor. <i>Nano Letters</i> , 2013, 13, 2370-2375.	4.5	112
63	Investigating the origin of Fermi level pinning in Ge Schottky junctions using epitaxially grown ultrathin MgO films. <i>Applied Physics Letters</i> , 2010, 96, .	1.5	111
64	Topological spintronics and magnetoelectronics. <i>Nature Materials</i> , 2022, 21, 15-23.	13.3	101
65	Exchange bias switching in an antiferromagnet/ferromagnet bilayer driven by spin-orbit torque. <i>Nature Electronics</i> , 2020, 3, 757-764.	13.1	99
66	Room-Temperature Skyrmions in an Antiferromagnet-Based Heterostructure. <i>Nano Letters</i> , 2018, 18, 980-986.	4.5	98
67	Enhancement of voltage-controlled magnetic anisotropy through precise control of Mg insertion thickness at CoFeB MgO interface. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	92
68	Role of dimensional crossover on spin-orbit torque efficiency in magnetic insulator thin films. <i>Nature Communications</i> , 2018, 9, 3612.	5.8	84
69	Normal-incidence Ge quantum-dot photodetectors at 1.5 μ m based on Si substrate. <i>Applied Physics Letters</i> , 2002, 80, 1189-1191.	1.5	82
70	Band alignments and photon-induced carrier transfer from wetting layers to Ge islands grown on Si(001). <i>Applied Physics Letters</i> , 2001, 78, 1763-1765.	1.5	81
71	Comparative Evaluation of Spin-Transfer-Torque and Magnetoelectric Random Access Memory. <i>IEEE Journal on Emerging and Selected Topics in Circuits and Systems</i> , 2016, 6, 134-145.	2.7	81
72	Spin-Orbit Torque Switching of a Nearly Compensated Ferrimagnet by Topological Surface States. <i>Advanced Materials</i> , 2019, 31, e1901681.	11.1	81

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73	Magneto-optical investigation of spin-orbit torques in metallic and insulating magnetic heterostructures. <i>Nature Communications</i> , 2015, 6, 8958.	5.8	80
74	Stable silver nanoclusters electrochemically deposited on nitrogen-doped graphene as efficient electrocatalyst for oxygen reduction reaction. <i>Journal of Power Sources</i> , 2015, 274, 1173-1179.	4.0	78
75	Manipulating Surface-Related Ferromagnetism in Modulation-Doped Topological Insulators. <i>Nano Letters</i> , 2013, 13, 4587-4593.	4.5	77
76	Spintronics Based on Topological Insulators. <i>Spin</i> , 2016, 06, 1640001.	0.6	77
77	Stateful Reconfigurable Logic via a Single-Voltage-Gated Spin Hall-Effect Driven Magnetic Tunnel Junction in a Spintronic Memory. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 4295-4301.	1.6	76
78	Creation and annihilation of non-volatile fixed magnetic skyrmions using voltage control of magnetic anisotropy. <i>Nature Electronics</i> , 2020, 3, 539-545.	13.1	76
79	Dzyaloshinskii-Moriya Interaction across an Antiferromagnet-Ferromagnet Interface. <i>Physical Review Letters</i> , 2017, 119, 027202.	2.9	75
80	Plasmonic effects for light concentration in organic photovoltaic thin films induced by hexagonal periodic metallic nanospheres. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	73
81	Giant interfacial perpendicular magnetic anisotropy in MgO/CoFe/capping layer structures. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	73
82	Magnetolectric spin wave amplifier for spin wave logic circuits. <i>Journal of Applied Physics</i> , 2009, 106, .	1.1	72
83	Interfacial control of Dzyaloshinskii-Moriya interaction in heavy metal/ferromagnetic metal thin film heterostructures. <i>Physical Review B</i> , 2016, 94, .	1.1	72
84	Current-driven perpendicular magnetization switching in Ta/CoFeB/[TaOx or MgO/TaOx] films with lateral structural asymmetry. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	71
85	Electric-poling-induced magnetic anisotropy and electric-field-induced magnetization reorientation in magnetoelectric Ni/(011) [Pb(Mg _{1/3} Nb _{2/3})O ₃] _(1-x) -[PbTiO ₃] _x heterostructure. <i>Journal of Applied Physics</i> , 2011, 109, 07D732.	1.1	67
86	Magnetic memory driven by topological insulators. <i>Nature Communications</i> , 2021, 12, 6251.	5.8	67
87	Part-per-million quantization and current-induced breakdown of the quantum anomalous Hall effect. <i>Physical Review B</i> , 2018, 98, .	1.1	65
88	Large Tunneling Magnetoresistance in VSe ₂ /MoS ₂ Magnetic Tunnel Junction. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 17647-17653.	4.0	65
89	Chiral Symmetry Breaking for Deterministic Switching of Perpendicular Magnetization by Spin-Orbit Torque. <i>Nano Letters</i> , 2021, 21, 515-521.	4.5	64
90	Layer Engineering of 2D Semiconductor Junctions. <i>Advanced Materials</i> , 2016, 28, 5126-5132.	11.1	63

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91	Direct structural evidences of Mn ₁₁ Ge ₈ and Mn ₅ Ge ₂ clusters in Ge _{0.96} Mn _{0.04} thin films. Applied Physics Letters, 2008, 92, .	1.5	61
92	Exchange-biasing topological charges by antiferromagnetism. Nature Communications, 2018, 9, 2767.	5.8	61
93	Spatially Resolved Photoexcited Charge-Carrier Dynamics in Phase-Engineered Monolayer MoS ₂ . ACS Nano, 2015, 9, 840-849.	7.3	58
94	Spin-orbit torques in perpendicularly magnetized Ir ₂₂ Mn ₇₈ /Co ₂₀ Fe ₆₀ B ₂₀ /MgO multilayer. Applied Physics Letters, 2016, 109, .	1.5	58
95	Issues of Nanoelectronics: A Possible Roadmap. Journal of Nanoscience and Nanotechnology, 2002, 2, 235-266.	0.9	57
96	Enhanced Field Emission Properties from CNT Arrays Synthesized on Inconel Superalloy. ACS Applied Materials & Interfaces, 2014, 6, 1986-1991.	4.0	57
97	Suspended few-layer graphene beam electromechanical switch with abrupt on-off characteristics and minimal leakage current. Applied Physics Letters, 2011, 99, .	1.5	56
98	Effect of the oxide layer on current-induced spin-orbit torques in Hf CoFeB MgO and Hf CoFeB TaOx structures. Applied Physics Letters, 2015, 106, .	1.5	55
99	Spiral Growth of SnSe ₂ Crystals by Chemical Vapor Deposition. Advanced Materials Interfaces, 2016, 3, 1600383.	1.9	55
100	Alloying, elemental enrichment, and interdiffusion during the growth of Ge(Si)/Si(001) quantum dots. Physical Review B, 2002, 65, .	1.1	54
101	Atomic-Scale Magnetism of Cr-Doped Bi ₂ Se ₃ Thin Film Topological Insulators. ACS Nano, 2015, 9, 10237-10243.	7.3	54
102	Electrical spin injection and transport in semiconductor nanowires: challenges, progress and perspectives. Nanoscale, 2015, 7, 4325-4337.	2.8	52
103	High-Current Gain Two-Dimensional MoS ₂ -Base Hot-Electron Transistors. Nano Letters, 2015, 15, 7905-7912.	4.5	52
104	Deterministic Spin-Orbit Torque Switching by a Light-Metal Insertion. Nano Letters, 2020, 20, 3703-3709.	4.5	52
105	Metallic nanomesh electrodes with controllable optical properties for organic solar cells. Applied Physics Letters, 2012, 100, .	1.5	51
106	Topology-Dependent Brownian Gyromotion of a Single Skyrmion. Physical Review Letters, 2020, 125, 027206.	2.9	50
107	Experimental Demonstration of Spintronic Broadband Microwave Detectors and Their Capability for Powering Nanodevices. Physical Review Applied, 2019, 11, .	1.5	49
108	Spin-orbit torque from a ferromagnetic metal. Physical Review B, 2019, 99, .	1.1	49

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109	Memory effects related to deep levels in metal-oxide-semiconductor structure with nanocrystalline Si. Applied Physics Letters, 2002, 80, 2502-2504.	1.5	48
110	Electrical field control magnetic phase transition in nanostructured $\text{Mn}_x\text{Ge}_{1-x}$. Applied Physics Letters, 2007, 90, 012501.	1.5	48
111	Joule Heating Effect on Field-Free Magnetization Switching by Spin-Orbit Torque in Exchange-Biased Systems. Physical Review Applied, 2017, 7, .	1.5	48
112	Vertically Aligned Carbon Nanotubes/Graphene Hybrid Electrode as a TCO- and Pt-Free Flexible Cathode for Application in Solar Cells. Journal of Materials Chemistry A, 2014, 2, 20902-20907.	5.2	47
113	Thermally stable voltage-controlled perpendicular magnetic anisotropy in $\text{Mo} \text{CoFeB} \text{MgO}$ structures. Applied Physics Letters, 2015, 107, .	1.5	47
114	Voltage-controlled magnetoelectric memory and logic devices. MRS Bulletin, 2018, 43, 970-977.	1.7	47
115	Thickness-dependent bulk electronic properties in Bi_2Se_3 thin films revealed by infrared spectroscopy. Physical Review B, 2013, 88, .	1.1	45
116	Atomic-Monolayer Two-Dimensional Lateral Quasi-Heterojunction Bipolar Transistors with Resonant Tunneling Phenomenon. ACS Nano, 2017, 11, 11015-11023.	7.3	45
117	Field-Free Spin-Orbit Torque Switching of Perpendicular Magnetization by the Rashba Interface. ACS Applied Materials & Interfaces, 2019, 11, 39369-39375.	4.0	45
118	Ternary $\text{Cu}_{1-x}\text{Se}_x$: Towards Ultra-Thin Layered Photodetectors and Photovoltaic Devices. Advanced Materials, 2014, 26, 7666-7672.	11.1	43
119	Observing the interplay between surface and bulk optical nonlinearities in thin van der Waals crystals. Scientific Reports, 2016, 6, 22620.	1.6	42
120	Topological Transitions Induced by Antiferromagnetism in a Thin-Film Topological Insulator. Physical Review Letters, 2018, 121, 096802.	2.9	42
121	Impact of gate work-function on memory characteristics in $\text{Al}_2\text{O}_3/\text{HfO}_x/\text{Al}_2\text{O}_3/\text{graphene}$ charge-trap memory devices. Applied Physics Letters, 2012, 100, .	1.5	41
122	Low-Cost, Large-Area, Facile, and Rapid Fabrication of Aligned ZnO Nanowire Device Arrays. ACS Applied Materials & Interfaces, 2016, 8, 13466-13471.	4.0	41
123	Atomic-Monolayer MoS_2 Band-to-Band Tunneling Field-Effect Transistor. Small, 2016, 12, 5676-5683.	5.2	41
124	Proximity-Induced Magnetic Order in a Transferred Topological Insulator Thin Film on a Magnetic Insulator. ACS Nano, 2018, 12, 5042-5050.	7.3	41
125	Ferrimagnetic Skyrmions in Topological Insulator/Ferrimagnet Heterostructures. Advanced Materials, 2020, 32, e2003380.	11.1	41
126	Alternate State Variables for Emerging Nanoelectronic Devices. IEEE Nanotechnology Magazine, 2009, 8, 66-75.	1.1	40

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127	Diode-MTJ Crossbar Memory Cell Using Voltage-Induced Unipolar Switching for High-Density MRAM. IEEE Electron Device Letters, 2013, 34, 753-755.	2.2	39
128	Direct growth of MoS ₂ single crystals on polyimide substrates. 2D Materials, 2017, 4, 021028.	2.0	39
129	Exploring interfacial exchange coupling and sublattice effect in heavy metal/ferrimagnetic insulator heterostructures using Hall measurements, x-ray magnetic circular dichroism, and neutron reflectometry. Physical Review B, 2019, 99, .	1.1	39
130	Influence of Edge Defects, Vacancies, and Potential Fluctuations on Transport Properties of Extremely Scaled Graphene Nanoribbons. IEEE Transactions on Electron Devices, 2012, 59, 3231-3238.	1.6	38
131	Scalable Transfer of Suspended Two-Dimensional Single Crystals. Nano Letters, 2015, 15, 5089-5097.	4.5	38
132	Mobile Néel skyrmions at room temperature: status and future. AIP Advances, 2016, 6, .	0.6	38
133	Strong Electrical Manipulation of Spin-Orbit Torque in Ferromagnetic Heterostructures. Advanced Electronic Materials, 2016, 2, 1600219.	2.6	37
134	Chiral transport along magnetic domain walls in the quantum anomalous Hall effect. Npj Quantum Materials, 2017, 2, .	1.8	37
135	A Van der Waals Interface Hosting Two Groups of Magnetic Skyrmions. Advanced Materials, 2022, 34, e2110583.	11.1	37
136	Strain-induced magnetization change in patterned ferromagnetic nickel nanostructures. Journal of Applied Physics, 2011, 109, 123903.	1.1	36
137	Spin-torque ferromagnetic resonance measurements utilizing spin Hall magnetoresistance in W/Co ₄₀ Fe ₄₀ B ₂₀ /MgO structures. Applied Physics Letters, 2016, 109, .	1.5	36
138	Large exchange splitting in monolayer graphene magnetized by an antiferromagnet. Nature Electronics, 2020, 3, 604-611.	13.1	36
139	Enhancing electric-field control of ferromagnetism through nanoscale engineering of high-T _c Mn _x Ge _{1-x} nanomesh. Nature Communications, 2016, 7, 12866.	5.8	35
140	Probing the low-temperature limit of the quantum anomalous Hall effect. Science Advances, 2020, 6, eaaz3595.	4.7	35
141	Direct Mapping of Charge Distribution during Lithiation of Ge Nanowires Using Off-Axis Electron Holography. Nano Letters, 2016, 16, 3748-3753.	4.5	34
142	3D Band Diagram and Photoexcitation of 2D-3D Semiconductor Heterojunctions. Nano Letters, 2015, 15, 5919-5925.	4.5	33
143	Effect of heavy metal layer thickness on spin-orbit torque and current-induced switching in Hf CoFeB MgO structures. Applied Physics Letters, 2016, 109, .	1.5	33
144	Normal-incidence epitaxial SiGeC photodetector near 1.3 μ m wavelength grown on Si substrate. Applied Physics Letters, 1996, 69, 2330-2332.	1.5	32

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145	Zero-field edge plasmons in a magnetic topological insulator. <i>Nature Communications</i> , 2017, 8, 1836.	5.8	32
146	N ₂ -Type Elliptical Skyrmions in a Laterally Asymmetric Magnetic Multilayer. <i>Advanced Materials</i> , 2021, 33, e2006924.	11.1	32
147	Strain-Mediated Spin-Orbit-Torque Switching for Magnetic Memory. <i>Physical Review Applied</i> , 2018, 10, .	1.5	31
148	Control of Spin-Wave Damping in YIG Using Spin Currents from Topological Insulators. <i>Physical Review Applied</i> , 2019, 11, .	1.5	30
149	Voltage-Controlled Magnetic Tunnel Junctions for Processing-In-Memory Implementation. <i>IEEE Electron Device Letters</i> , 2018, 39, 440-443.	2.2	29
150	Strongly Surface State Carrier-Dependent Spin-Orbit Torque in Magnetic Topological Insulators. <i>Advanced Materials</i> , 2020, 32, e1907661.	11.1	29
151	Coplanar waveguide radio frequency ferromagnetic parametric amplifier. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	28
152	Magneto-electric tuning of the phase of propagating spin waves. <i>Applied Physics Letters</i> , 2012, 101, .	1.5	28
153	Giant Charge-to-Spin Conversion Efficiency in SrTiO_3 -Based Electron Gas Interface. <i>Physical Review Applied</i> , 2019, 12, .	1.5	28
154	Engineering of tunnel junctions for prospective spin injection in germanium. <i>Applied Physics Letters</i> , 2009, 94, 242104.	1.5	27
155	Solid-Vapor Reaction Growth of Transition-Metal Dichalcogenide Monolayers. <i>Angewandte Chemie - International Edition</i> , 2016, 55, 10656-10661.	7.2	27
156	Analysis and Compact Modeling of Magnetic Tunnel Junctions Utilizing Voltage-Controlled Magnetic Anisotropy. <i>IEEE Transactions on Magnetics</i> , 2018, 54, 1-9.	1.2	27
157	Observation of Quantum Anomalous Hall Effect and Exchange Interaction in Topological Insulator/Antiferromagnet Heterostructure. <i>Advanced Materials</i> , 2020, 32, e2001460.	11.1	27
158	Single-spin sensing of domain-wall structure and dynamics in a thin-film skyrmion host. <i>Physical Review Materials</i> , 2019, 3, .	0.9	27
159	Interfacial Perpendicular Magnetic Anisotropy in Sub-20 nm Tunnel Junctions for Large-Capacity Spin-Transfer Torque Magnetic Random-Access Memory. <i>IEEE Magnetics Letters</i> , 2017, 8, 1-5.	0.6	25
160	Low-frequency noise in top-gated ambipolar carbon nanotube field effect transistors. <i>Applied Physics Letters</i> , 2008, 92, .	1.5	24
161	Spin-Torque Driven Switching Probability Density Function Asymmetry. <i>IEEE Transactions on Magnetics</i> , 2012, 48, 3818-3820.	1.2	24
162	Anomalous Nernst effect in Ir ₂₂ Mn ₇₈ /Co ₂₀ Fe ₆₀ B ₂₀ /MgO layers with perpendicular magnetic anisotropy. <i>Applied Physics Letters</i> , 2017, 111, .	1.5	24

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163	Fast photoresponse and high detectivity in copper indium selenide (CuIn ₇ Se ₁₁) phototransistors. 2D Materials, 2018, 5, 015001.	2.0	24
164	Failure Mechanism Analysis of SiC MOSFETs in Unclamped Inductive Switching Conditions. , 2019, , .		24
165	Colossal electric field control of magnetic anisotropy at ferromagnetic interfaces induced by iridium overlayer. Physical Review B, 2019, 99, .	1.1	24
166	Deficiency of the bulk spin Hall effect model for spin-orbit torques in magnetic-insulator/heavy-metal heterostructures. Physical Review B, 2017, 95, .	1.1	23
167	Spin-torque ferromagnetic resonance in $W/Co/Fe$ heterostructures. Physical Review Applied, 2017, 7, .	1.5	23
168	Annealing effects on the microstructure of Ge/Si(001) quantum dots. Applied Physics Letters, 2001, 79, 1258-1260.	1.5	22
169	Efficient Excitation of High-Frequency Exchange-Dominated Spin Waves in Periodic Ferromagnetic Structures. Physical Review Applied, 2017, 7, .	1.5	22
170	Predictive Materials Design of Magnetic Random-Access Memory Based on Nanoscale Atomic Structure and Element Distribution. Nano Letters, 2019, 19, 8621-8629.	4.5	22
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